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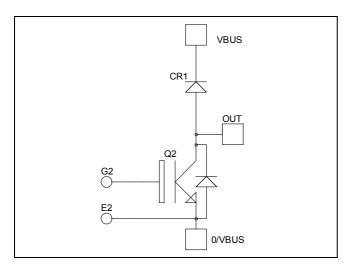






Boost chopper NPT IGBT Power Module

 $V_{CES} = 1200V$ $I_{C} = 300A$ @ Tc = 80°C

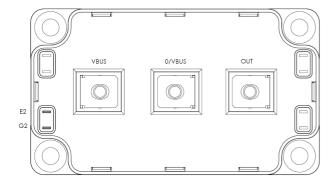


Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Non Punch Through (NPT) FAST IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit	
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V	
I_{C}	Continuous Collector Current	$T_c = 25^{\circ}C$	400	·	
	Continuous Conector Current	$T_c = 80$ °C	300	A	
I_{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	600		
V_{GE}	Gate – Emitter Voltage		±20	V	
P_{D}	Maximum Power Dissipation	$T_c = 25^{\circ}C$	1780	W	
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	600A @ 1200V		

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
Ţ	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_j = 25$ °C			500	1
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE} = 1200V$	$T_j = 125$ °C			750	μΑ
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		3.3	3.9	V
$V_{CE(sat)}$	Confector Emitter Saturation Voltage	$I_{\rm C} = 300 A$	$T_j = 125$ °C		4		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 12mA$		4.5		6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = \pm 20V, V_{CE} = 0V$				±1	μA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			21		nF
C_{oes}	Output Capacitance				2.9		
C_{res}	Reverse Transfer Capacitance				1.52		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)			120		
T_{r}	Rise Time	$V_{GE} = 15V$			50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 300A$ $R_G = 3\Omega$			310		ns
T_{f}	Fall Time				30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = 15V$ $V_{Bus} = 600V$ $I_{C} = 300A$ $R_{G} = 3\Omega$			130		ns
T_{r}	Rise Time				60		
$T_{d(off)}$	Turn-off Delay Time				360		
$T_{\rm f}$	Fall Time				40		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 600V$	$T_j = 125$ °C		25		T
E_{off}	Turn-off Switching Energy	$I_{C} = 300A$ $R_{G} = 3\Omega$	$T_j = 125$ °C		15		mJ

Chopper diode ratings and characteristics

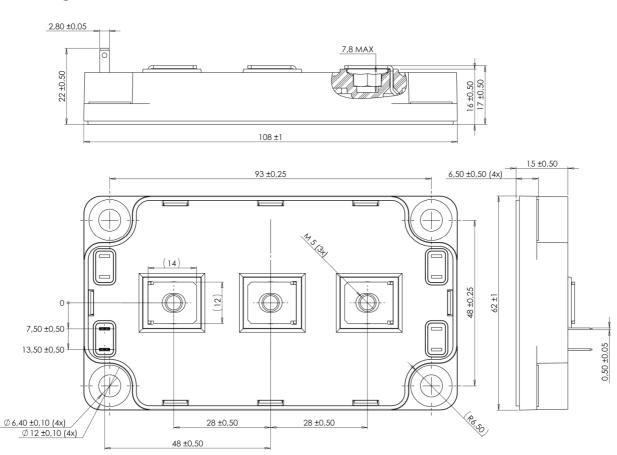
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
T	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25$ °C			750	^
I_{RM}			$T_j = 125$ °C			1000	μA
I_F	DC Forward Current		$Tc = 70^{\circ}C$		400		A
	Diode Forward Voltage	$I_F = 400A$			2.0	2.5	
$V_{\rm F}$		$I_{\rm F} = 800A$			2.5		V
		$I_F = 400A$	$T_j = 125$ °C		1.8		
t	Reverse Recovery Time	$I_F = 400A$ $V_R = 800V$	$T_j = 25$ °C		420		ns
t _{rr}			$T_j = 125$ °C		580		115
Q _{rr}	Reverse Recovery Charge	$di/dt = 800A/\mu s \qquad T_j = 25$	$T_j = 25$ °C		5		μС
Q rr			$T_{j} = 125^{\circ}C$		21.4		μС



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.07	°C/W
1\(\text{thJC}\)			Diode			0.16	C/ VV
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range Operating Case Temperature			-40		125	
$T_{\rm C}$				-40		100	
Torque	Mounting forque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	11.111
Wt	Package Weight					300	g

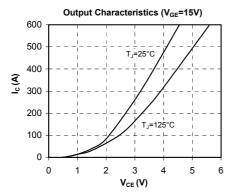
SP6 Package outline (dimensions in mm)

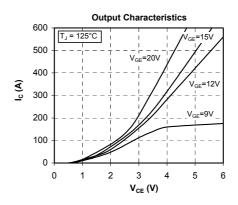


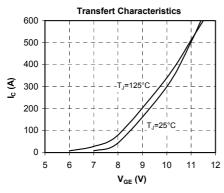
 $See \ application \ note \ APT0601 - Mounting \ Instructions \ for \ SP6 \ Power \ Modules \ on \ www.microsemi.com$

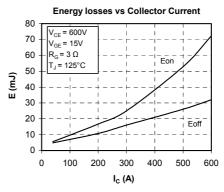


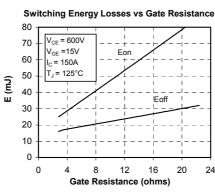
Typical Performance Curve

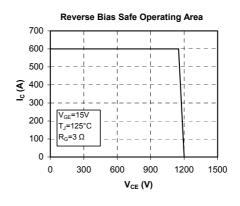


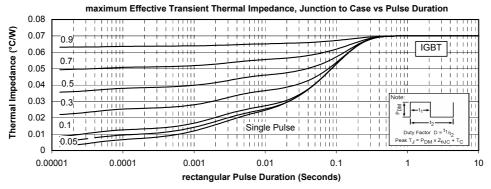




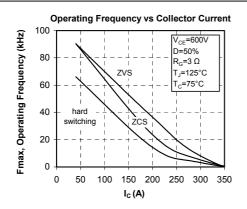


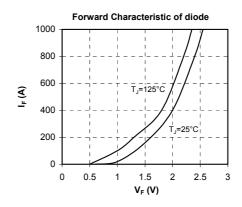


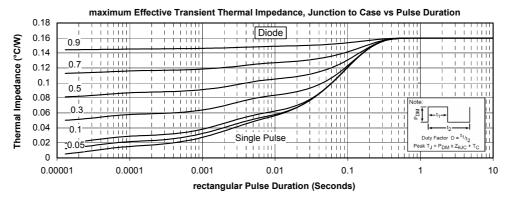














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